

## General Description

The WST3035 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST3035 meet the RoHS and Green Product requirement , with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

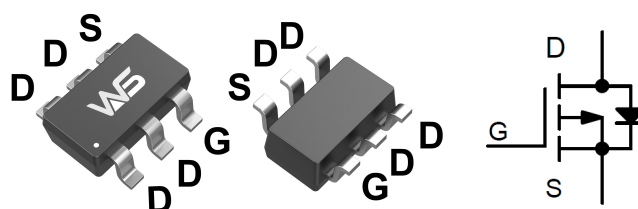
## Product Summary

| BVDSS | RDSON | ID    |
|-------|-------|-------|
| -30V  | 50mΩ  | -4.4A |

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## SOT- 23-6L Pin Configuration



## Absolute Maximum Ratings

| Symbol                | Parameter                                    | Rating     | Units       |
|-----------------------|--|------------|-------------|
| $V_{DS}$              | Drain-Source Voltage                         | -30        | V           |
| $V_{GS}$              | Gate-Source Voltage                          | $\pm 20$   | V           |
| $I_D@T_C=25^{\circ}C$ | Continuous Drain Current, $V_{GS} @ -4.5V^1$ | -4.4       | A           |
| $I_D@T_C=70^{\circ}C$ | Continuous Drain Current, $V_{GS} @ -4.5V^1$ | -3.0       | A           |
| $I_{DM}$              | Pulsed Drain Current <sup>2</sup>            | -14        | A           |
| $P_D@T_A=25^{\circ}C$ | Total Power Dissipation <sup>3</sup>         | 1          | W           |
| $T_{STG}$             | Storage Temperature Range                    | -55 to 150 | $^{\circ}C$ |
| $T_J$                 | Operating Junction Temperature Range         | -55 to 150 | $^{\circ}C$ |

## Thermal Data

| Symbol          | Parameter  | Typ. | Max. | Unit          |
|-----------------|--|------|------|---------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient <sup>1</sup> | ---  | 125  | $^{\circ}C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case <sup>1</sup>    | ---  | 80   | $^{\circ}C/W$ |

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

| Symbol                       | Parameter                                      | Conditions   | Min. | Typ.   | Max.      | Unit                   |
|------------------------------|--|--|------|--------|-----------|------------------------|
| $BV_{DSS}$                   | Drain-Source Breakdown Voltage                 | $V_{GS}=0V$ , $I_D=-250\mu A$                                      | -30  | ---    | ---       | V                      |
| $\Delta BV_{DSS}/\Delta T_J$ | $BV_{DSS}$ Temperature Coefficient             | Reference to $25^{\circ}\text{C}$ , $I_D=-1mA$                     | ---  | -0.014 | ---       | V/ $^{\circ}\text{C}$  |
| $R_{DS(ON)}$                 | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=-10V$ , $I_D=-3A$  | ---  | 50     | 60        | $m\Omega$              |
|                              |  | $V_{GS}=-4.5V$ , $I_D=-2A$   | ---  | 73     | 90        |                        |
| $V_{GS(th)}$                 | Gate Threshold Voltage                         | $V_{GS}=V_{DS}$ , $I_D=-250\mu A$                                  | -0.5 | -1.0   | -2.5      | V                      |
| $\Delta V_{GS(th)}$          | $V_{GS(th)}$ Temperature Coefficient           |  | ---  | 3.95   | ---       | mV/ $^{\circ}\text{C}$ |
| $I_{DSS}$                    | Drain-Source Leakage Current                   | $V_{DS}=-24V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$             | ---  | ---    | -1        | $\mu A$                |
|                              |  | $V_{DS}=-24V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$             | ---  | ---    | -5        |                        |
| $I_{GSS}$                    | Gate-Source Leakage Current                    | $V_{GS}=\pm 20V$ , $V_{DS}=0V$                                     | ---  | ---    | $\pm 100$ | nA                     |
| $g_{fs}$                     | Forward Transconductance                       | $V_{DS}=-5V$ , $I_D=-3A$   | ---  | 12.8   | ---       | S                      |
| $Q_g$                        | Total Gate Charge (-4.5V)                      | $V_{DS}=-15V$ , $V_{GS}=-4.5V$ , $I_D=-3A$                         | ---  | 12     | 14.3      | nC                     |
| $Q_{gs}$                     | Gate-Source Charge                             |  | ---  | 1.92   | 2.6       |                        |
| $Q_{gd}$                     | Gate-Drain Charge                              |  | ---  | 3.3    | 4.3       |                        |
| $T_{d(on)}$                  | Turn-On Delay Time                             | $V_{DD}=-15V$ ,<br>$V_{GS}=-4.5V$ , $R_G=3.3\Omega$ ,<br>$I_D=-3A$ | ---  | 5.9    | 11.2      | ns                     |
| $T_r$                        | Rise Time                                      |  | ---  | 42     | 73        |                        |
| $T_{d(off)}$                 | Turn-Off Delay Time                            |  | ---  | 34     | 67        |                        |
| $T_f$                        | Fall Time                                      |  | ---  | 19     | 36        |                        |
| $C_{iss}$                    | Input Capacitance                              | $V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1MHz$                             | ---  | 895    | 1200      | pF                     |
| $C_{oss}$                    | Output Capacitance                             |  | ---  | 134    | 160       |                        |
| $C_{rss}$                    | Reverse Transfer Capacitance                   |  | ---  | 120    | 151       |                        |

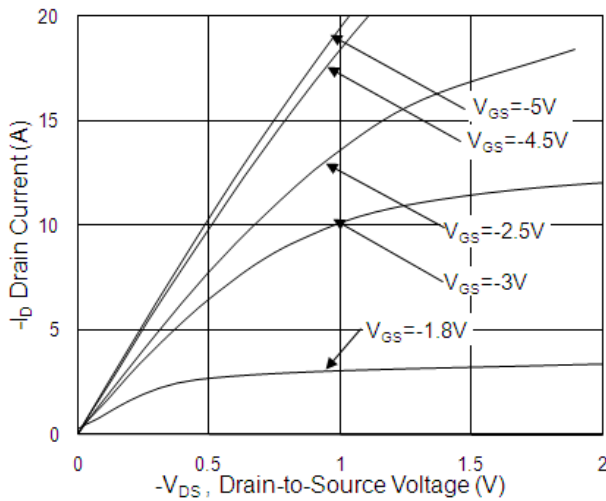
**Diode Characteristics**

| Symbol   | Parameter                                | Conditions  | Min. | Typ. | Max. | Unit |
|----------|--|---|------|------|------|------|
| $I_S$    | Continuous Source Current <sup>1,4</sup> | $V_G=V_D=0V$ , Force Current                              | ---  | ---  | -1   | A    |
| $I_{SM}$ | Pulsed Source Current <sup>2,4</sup>     |   | ---  | ---  | -14  | A    |
| $V_{SD}$ | Diode Forward Voltage <sup>2</sup>       | $V_{GS}=0V$ , $I_S=-1A$ , $T_J=25^{\circ}\text{C}$        | ---  | ---  | -1   | V    |
| $t_{rr}$ | Reverse Recovery Time                    | $I_F=-3A$ , $dI/dt=100A/\mu s$ , $T_J=25^{\circ}\text{C}$ | ---  | 23   | ---  | nS   |
| $Q_{rr}$ | Reverse Recovery Charge                  |   | ---  | 7.2  | ---  | nC   |

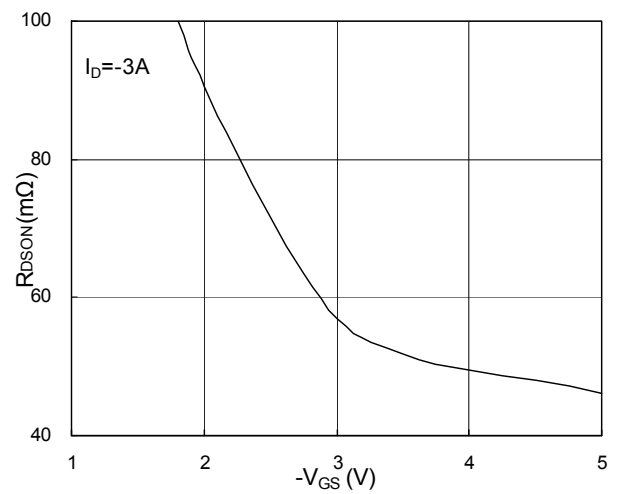
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper,  $t < 10\text{sec}$ .
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

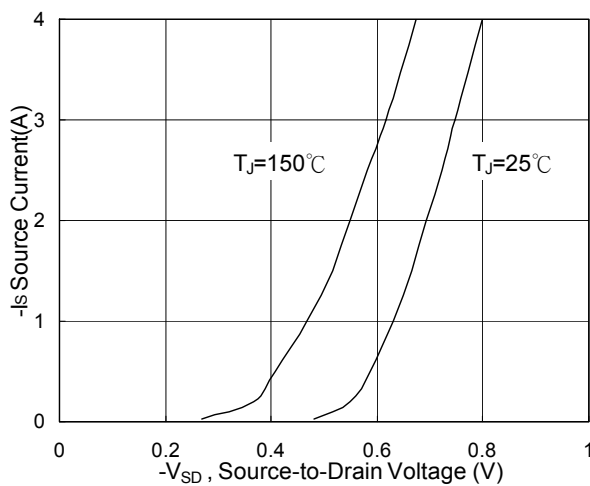
## Typical Characteristics



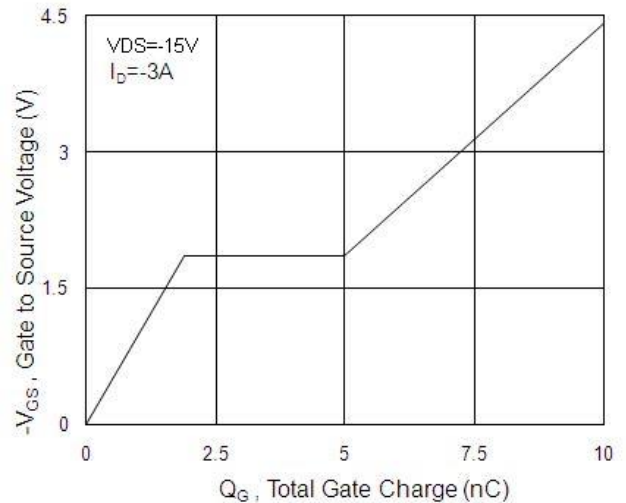
**Fig.1 Typical Output Characteristics**



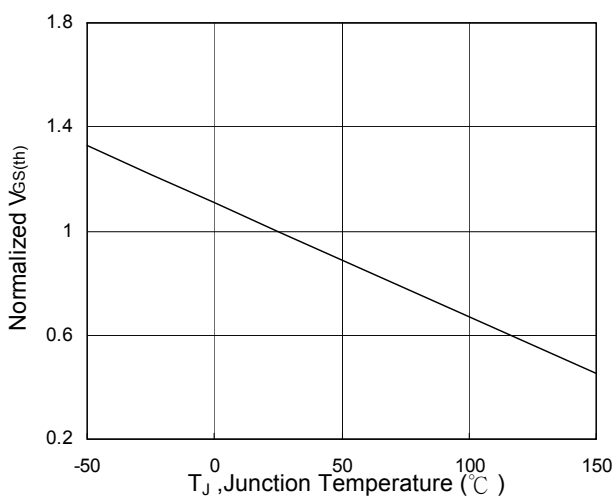
**Fig.2 On-Resistance vs. G-S Voltage**



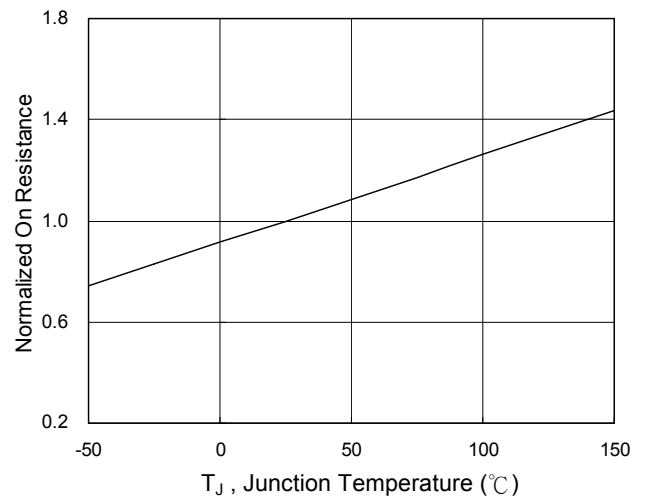
**Fig.3 Forward Characteristics of Reverse**



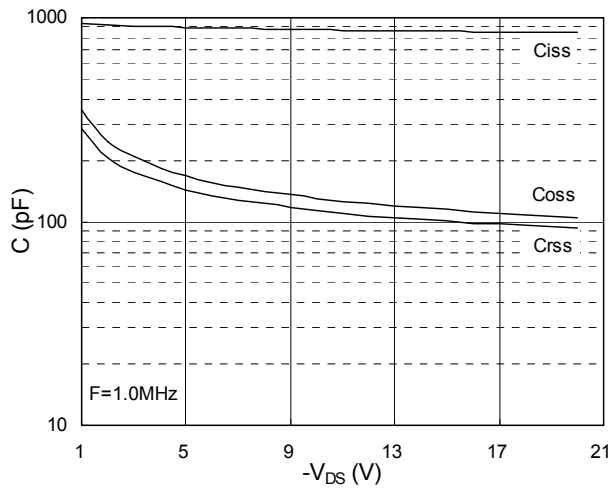
**Fig.4 Gate-charge Characteristics**



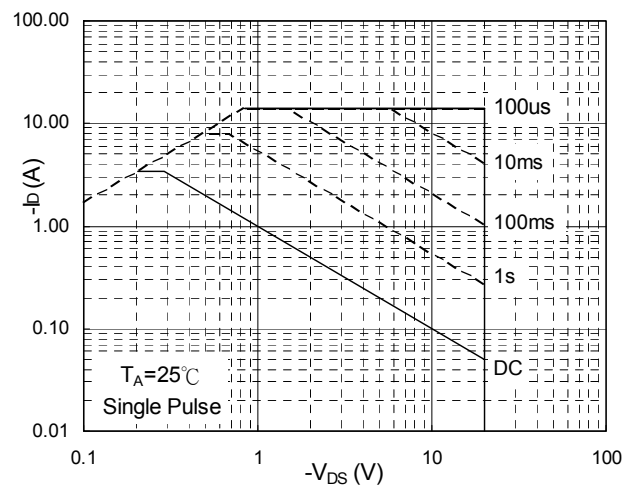
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



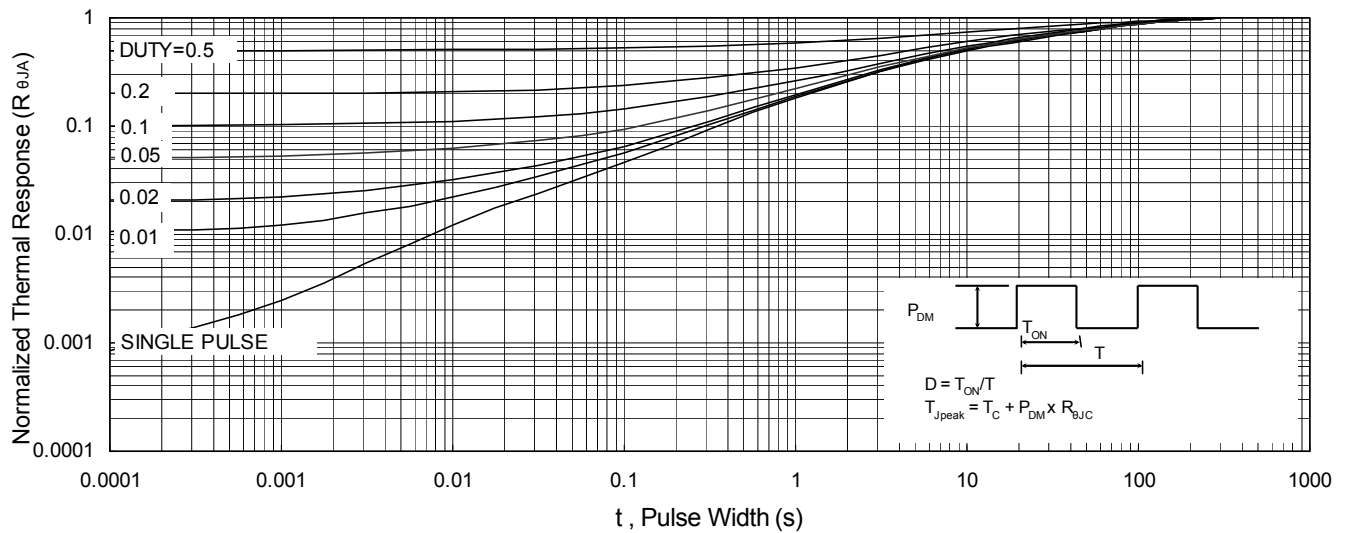
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



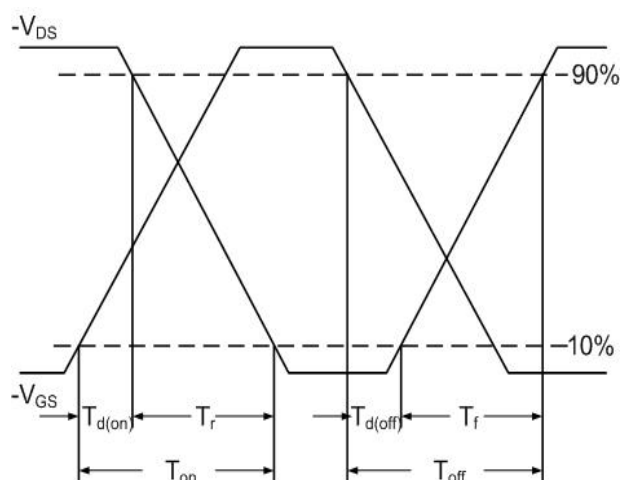
**Fig.7 Capacitance**



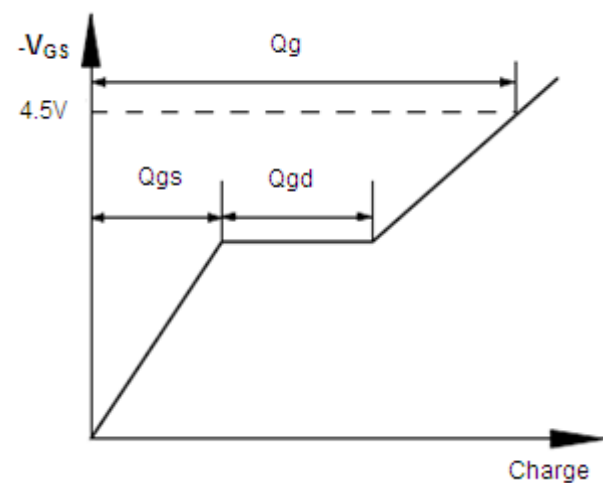
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**

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